Time: 3 Hours 1

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## II Semester Diploma Examination, April/May-2017

## BASICS OF SEMI CONDUCTOR DEVICES

3 Hours ]	Max. Marks : 100
<ul><li>(i) Answer any SIX questions from PART-A.</li><li>(ii) Answer any SEVEN question from PART-B.</li></ul>	
PART – A  fine doping. Explain atomic structure of p-type semiconductor	5 × 6 = 30 BETA CONSOLE! 5
plain working of NPN Transistor.	Diploma - [All Branches]  Beta Console Education  34
etch and explain input characteristics of transistor in CE mode	5
plain CMOSFET as an inverter.	Diploma Question Papers [2015-19]  Beta Console Education 5
mpare BJT and FET.	5
t the applications of Schotky diode and GUNN diode.	5
fine IC's. Mention advantages.	5
ite a short note on Solar cell.	5
plain the terms photoemission and photoconduction.  1 of 2	5  Turn over
	(i) Answer any SIX questions from PART-A. (ii) Answer any SEVEN question from PART-B.  PART – A  If the doping. Explain atomic structure of p-type semiconductor plain working of NPN Transistor.  etch and explain input characteristics of transistor in CE mode plain CMOSFET as an inverter.  In the applications of Schotky diode and GUNN diode.  It the applications of Schotky diode and GUNN diode.  It is a short note on Solar cell.

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